PATENT COOPERATION TREATY

PCT

INTERNATIONAL SEARCH REPORT

(PCT Article 18 and Rules 43 and 44)

Applicant's or agent's file reference 1038-12 PCT		see Form PCT/ISA/220 as well as, where applicable, item 5 below.			
International application No. PCT/US05/09383	International filing date (day/month/year) 22 March 2005 (22.03.2005)	(Earliest) Priority Date (day/month/year) 22 March 2004 (22.03.2004)			
Applicant RESEARCH FOUNDATION OF THE CITY UNIVERSITY OF NEW					
This international search report has been prepared by this International Searching Authority and is transmitted to the applicant according to Article 18. A copy is being transmitted to the International Bureau. This international search report consists of a total of					
may, within one month from	, according to Rule 38.2(b), by this Authority	as it appears in Box No. IV. The applicant ch report, submit comments to this Authority.			
as suggested by the as selected by this A	Authority, because the applicant failed to sugg				
b. as selected by this A	Authority, because this figure better characterioublished with the abstract.	izes the invention.			

Form PCT/ISA/210 (first sheet) (April 2005)

3.

INTERNATIONAL SEARCH REPORT

International application No.

PCT/US05/09383

Roy IV	TEYT	OF THE	ABSTRACT	(Continuation	of Item 5	of the first sheet)

An optical device (MSM) for sensing an incident optical wave within a wavelength range includes a first array and a second array of electrodes (10) superposed on a substrate (16), and a sensor connected to the contacts. The arrays are interdigitated. Each array includes its own parameters: contact width, contact thickness, groove width, and a groove dielectric constant. A structure assosciated with the arrays resonantly couples the incident wave and a local electromagnetic resonance or hybrid mode including at least a surface plasmon cavity mode (CM). For couplin the CM, an aspacet ration of contact thickness to spacing between electrodes is at least 1. A preferred structure for coupling a hybrid mode for high bandwidth and responsivity includs a higher dielectric constant in alternating grooves. The substrate may include silicon, including silicon-on-insulator (SOI). Sn SOI device having alternating grooves with a highter dielectric, e.g. silicon oxide, provides .25 A/W and 30 GHz bandwidth.	
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INTERNATIONAL SEARCH REPORT

International application No.

PCT/US05/09383

A. CLAS					
USPC: 250/214.1,214R;257/184,189,441-444,448,449,457-459 According to International Patent Classification (IPC) or to both national classification and IPC					
B. FIEL	DS SEARCHED				
Minimum documentation searched (classification system followed by classification symbols) U.S.: 250/214.1,214R; 257/184,189,441-444,448,449,457-459					
Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched NONE					
Electronic data base consulted during the international search (name of data base and, where practicable, search terms used) Please See Continuation Sheet					
C. DOC	UMENTS CONSIDERED TO BE RELEVANT				
Category *	Citation of document, with indication, where a	appropriate,	of the relevant passages	Relevant to claim No.	
A, P	US 6,713,832 A (PARDO et al) 30 April 2004 (30.	04.2004), s	ee entire document.	1-31	
Α	US 5,945,720 A (ISHII et al) 31 August 1999 (31.08.1999), see entire document.		1-31		
Further	documents are listed in the continuation of Box C.		See patent family annex.		
"A" document	defining the general state of the art which is not considered to be ar relevance	"T"	later document published after the inter date and not in conflict with the applica principle or theory underlying the inver document of particular relevance; the ci	tion but cited to understand the	
"E" earlier app	dication or patent published on or after the international filing date	~	considered novel or cannot be considered when the document is taken alone		
	which may throw doubts on priority claim(s) or which is cited to he publication date of another citation or other special reason (as	"Y"	document of particular relevance; the cl considered to involve an inventive step combined with one or more other such	when the document is	
"O" document	referring to an oral disclosure, use, exhibition or other means		being obvious to a person skilled in the	arı	
priority da	published prior to the international filing date but later than the te claimed	~& ~	document member of the same patent fa	mily	
	Date of the actual completion of the international search Date of mailing of the international search report 3 1 AUG 2006			report	
	Name and mailing address of the ISA/US Authorized officer \ Authorized \(\text{Authorized officer} \)			Reco	
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Alexandria. Virginia 22313-1450 Facsimile No. (571) 273-3201 Telephone No. 571-272-2434					

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INTERNATIONAL SEARCH REPORT	International application No. PCT/US05/09383
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Continuation of B. FIELDS SEARCHED Item 3: U.S. PTO EAST DATABASES: search terms: (metal near2 semiconduct\$4 near2 metal or metal-semiconduct\$4-met	al or msm) and electrode and (plasmon near2 wave)

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